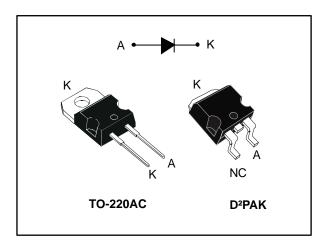


STPSC10H065-Y

Automotive 650 V power Schottky silicon carbide diode

Datasheet - production data



Features

- AEC-Q101 qualified
- No or negligible reverse recovery
- Switching behavior independent of temperature
- Dedicated to PFC applications
- High forward surge capability
- PPAP capable
- ECOPACK®2 compliant component

Description

The SiC diode is an ultra high performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide band gap material allows the design of a Schottky diode structure with a 650 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

Especially suited for use in PFC applications, this ST SiC diode will boost performance in hard switching conditions. Its high forward surge capability ensures good robustness during transient phases.

Table 1: Device summary

Symbol	Value
I _{F(AV)}	10 A
V _{RRM}	650 V
T _j (max.)	175 °C

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1 Characteristics

Table 2: Absolute ratings (limiting values at 25 °C, unless otherwise specified)

Symbol	Pa	Value	Unit	
V _{RRM}	Repetitive peak reverse voltage	T _j = -40 to +175 °C	650	V
I _{F(RMS)}	Forward rms current		22	Α
I _{F(AV)}	Average forward current	Tc = 135 °C ⁽¹⁾ , DC	10	Α
I _{FRM}	Repetitive peak forward current	$T_c = 135 ^{\circ}\text{C}, T_j = 175 ^{\circ}\text{C}, \delta = 0.1$	41	Α
		t_p = 10 ms sinusoidal, T_c = 25 °C	90	
I _{FSM}	I _{FSM} Surge non repetitive forward	Surge non repetitive forward $t_p = 10$ ms sinusoidal, $T_c = 125$ °C current		Α
	Carron	t_p = 10 µs square, T_c = 25 °C	470	
T _{stg}	Storage temperature range		-55 to +175	°C
Tj	Operating junction temperature ⁽²⁾		-40 to +175	°C

Notes:

Table 3: Thermal parameters

Symbol	Parameter -		Value	
Syllibol			Max.	Unit
R _{th(j-c)}	Junction to case	1.25	1.5	°C/W

Table 4: Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _R ⁽¹⁾	Poverse leakage ourrent	T _j = 25 °C	$V_R = V_{RRM}$	1	9	100	μA
IR	I _R ⁽¹⁾ Reverse leakage current	T _j = 150 °C		1	85	425	
V _F ⁽²⁾	Converd voltage drep	T _j = 25 °C	I _F = 10 A	-	1.56	1.75	V
VF ⁽²⁾	Forward voltage drop	T _j = 150 °C		•	1.98	2.5	

Notes:

 $^{(1)} Pulse$ test: t_p = 10 ms, $\delta < 2\%$

 $^{(2)}$ Pulse test: t_p = 500 μ s, δ < 2%

To evaluate the conduction losses, use the following equation:

$$P = 1.35 \text{ x } I_{F(AV)} + 0.115 \text{ x } I_{F^2(RMS)}$$

 $[\]ensuremath{^{(1)}}\mbox{Value}$ based on $R_{th(j\text{-}c)}$ max.

 $^{^{(2)}(}dP_{tot}/dT_j) < (1/R_{th(j\text{-}a)}) \ condition \ to \ avoid \ thermal \ runaway \ for \ a \ diode \ on \ its \ own \ heatsink.$

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Table 5: Dynamic electrical characteristics

Symbol	Parameter	Test conditions	Тур.	Unit
$Q_{Cj}^{(1)}$	Total capacitive charge	V _R = 400 V	28.5	nC
C _j	Total capacitance	$V_R = 0 \text{ V}, T_c = 25 \text{ °C}, F = 1 \text{ MHz}$	480	٦
		$V_R = 400 \text{ V}, T_c = 25 \text{ °C}, F = 1 \text{ MHz}$	48	pF

Notes:

 $^{^{(1)} \}rm Most$ accurate value for the capacitive charge: $Q_{cj} = \int_0^{V_{OUT}} C_J(V_R) \bullet dV_R$

Characteristics STPSC10H065-Y

Characteristics (curves) 1.1

Figure 1: Forward voltage drop versus forward current (typical values, low level)

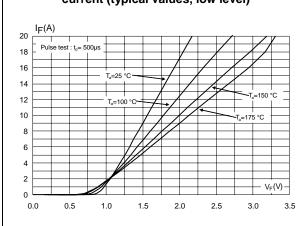


Figure 2: Forward voltage drop versus forward current (typical values, high level)

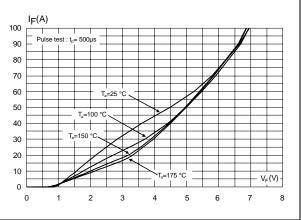


Figure 3: Reverse leakage current versus reverse voltage applied (typical values)

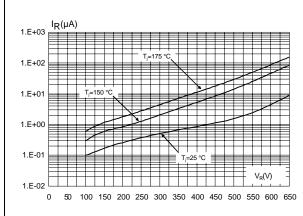


Figure 4: Peak forward current versus case temperature

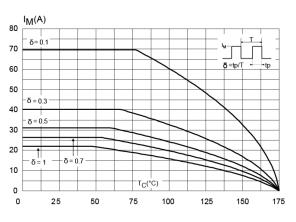
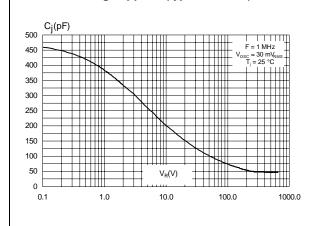
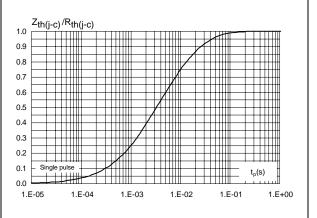


Figure 5: Junction capacitance versus reverse voltage applied (typical values)

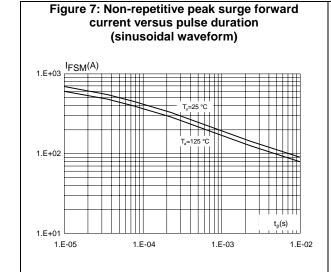


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Figure 6: Relative variation of thermal impedance junction to case versus pulse duration



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voltage applied (typical values) Q_{cj}(nC) V_R (V)

Figure 8: Total capacitive charges versus reverse

Figure 9: Thermal resistance junction to ambient versus copper surface under tab for D2PAK package (typical values) $R_{th(j-a)}(^{\circ}C/W)$ Epoxy printed board FR4, e_{CU} = 35 μm $S_{\text{Cu}}(\text{cm}^2)$

2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.55 N·m
- Maximum torque value: 0.7 N⋅m

2.1 D²PAK package information

SEATING PLANE

COPLANARITY A1

COPLANARITY A1

CAUGE PLANE

V2

Figure 10: D²PAK package outline

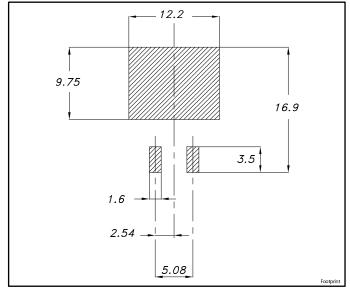
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Table 6: D²PAK package mechanical data

Table 6: D'PAK package mechanical data							
	Dimensions						
Ref.		Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А	4.40		4.60	0.173		0.181	
A1	0.03		0.23	0.001		0.009	
b	0.70		0.93	0.028		0.037	
b2	1.14		1.70	0.045		0.067	
С	0.45		0.60	0.018		0.024	
c2	1.23		1.36	0.048		0.053	
D	8.95		9.35	0.352		0.368	
D1	7.50	7.75	8.00	0.295	0.305	0.315	
D2	1.10	1.30	1.50	0.043	0.051	0.060	
Е	10		10.40	0.394		0.409	
E1	8.50	8.70	8.90	0.335	0.343	0.346	
E2	6.85	7.05	7.25	0.266	0.278	0.282	
е		2.54			0.100		
e1	4.88		5.28	0.190		0.205	
Н	15		15.85	0.591		0.624	
J1	2.49		2.69	0.097		0.106	
L	2.29		2.79	0.090		0.110	
L1	1.27		1.40	0.049		0.055	
L2	1.30		1.75	0.050		0.069	
R		0.4			0.015		
V2	0°		8°	0°		8°	

Figure 11: D²PAK recommended footprint (dimensions are in mm)





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2.2 TO-220AC package information

Figure 12: TO-220AC package outline

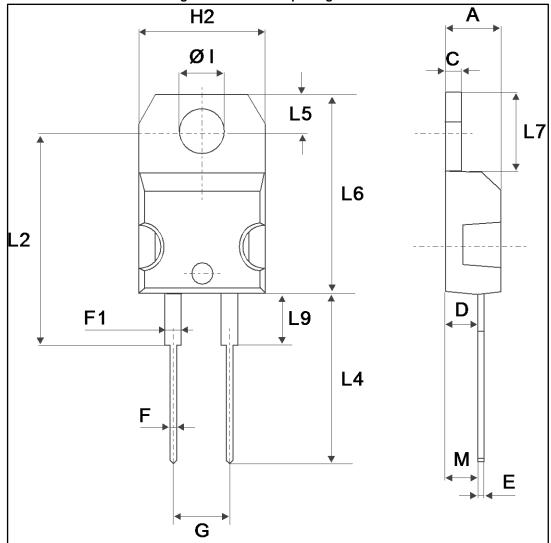


Table 7: TO-220AC package mechanical data

	Dimensions					
Ref.	Millin	neters	Inches			
	Min.	Max.	Min.	Max.		
А	4.40	4.60	0.173	0.181		
С	1.23	1.32	0.048	0.051		
D	2.40	2.72	0.094	0.107		
E	0.49	0.70	0.019	0.027		
F	0.61	0.88	0.024	0.034		
F1	1.14	1.70	0.044	0.066		
G	4.95	5.15	0.194	0.202		
H2	10.00	10.40	0.393	0.409		
L2	16.40	O typ.	0.645 typ.			
L4	13.00	14.00	0.511	0.551		
L5	2.65	2.95	0.104	0.116		
L6	15.25	15.75	0.600	0.620		
L7	6.20	6.60	0.244	0.259		
L9	3.50	3.93	0.137	0.154		
М	2.6 typ.		0.102 typ.			
Diam	3.75	3.85	0.147	0.151		

Ordering information STPSC10H065-Y

3 Ordering information

Table 8: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPSC10H065GY-TR	PSC10H065GY	D²PAK	1.48 g	1000	Tape and reel
STPSC10H065DY	PSC10H065DY	TO-220AC	1.86 g	50	Tube

4 Revision history

Table 9: Document revision history

Date	Revision	Changes
26-Jun-2014	1	First issue.
19-Sep-2014	2	Updated Table 8.
24-Sep-2015	3	Added device in D2PAK. Updated the entire document accordingly.
06-Feb-2017	4	Updated D ² PAK package information section.

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